King Fahd University of Petroleum & Minerals Electrical Engineering Department EE203: Electronics I (102)

| Instructor Information | | Dr. Oualid Hammi | Office 59/0012-5 | Phone: 7394 | Email: ohammi@kfupm.edu.sa | | Office Hours SMW: 9:30AM to 10:30AM or by appointment | |
|---------------------------|----------------------|---|---|--------------------|-------------------------------------|-------------------|--|----------------------------|
| | | | James 57, 5512 5 | - 110110. 707 1 | | | | |
| Course Information | | Text | Text Grading | | | | Attendance | |
| | | Microelectronic Circuits 5 th ed Sedra & Smith | (1) | | | Final Exam 30% | 6 unexcused absences → Warning 9 unexcused absences → DN | |
| | Week | | Topics to cover | | | Ch | Sec | Lab Activity |
| 1 | Feb 12 – | Diodes: Introduction, Idea operation of the diode. | eal diode, PN junction, Terminal characteristics of the diode, Physical | | | 3 | 1, 2, 7 | No Lab |
| 2 | Feb 19 - 2 | Graphical and analytical d | ode circuits analysis, Diode Models, the Zener diode. | | | 3 | 3.1-3.3, 3.5, 3.6, 4.1, 4.2 | Exp 1: Lab Equipment |
| 3 | Feb26 -Mar | | Diode applications: half and Full-wave rectifiers, Limiting and Clamping circuits and voltage oublers. Field-Effect Transistors (FETs): Device structure and operation. | | | 3 4 | 5.1-5.4, 6 1.1-1.5 | Exp 2: PSPICE |
| 4 | March 5 | PMOS structure and opera MOSFET Circuits at DC. | ion, CMOS structure, Current -Voltage Characteristic, Role of substrate, | | | e, 4 | 1.6-1.8, 2.1-2.5, 3 | Exp 3: Diode Applications |
| 5 | March 12 - | The MOSFET as amplifier CG and CD). | The MOSFET as amplifier, Biasing, small signal operation and models, Single stage amplifier (CS, CG and CD). | | | | 4-7 | No Lab |
| Exa | m 1 Saturday | March 19 (6:00-8:00 pm). Exam | location: Building 59 room 2001 f | or section 1 and | room 2002 for se | ection 2. | | |
| 6 | March 19 - | 21181 211181 11111 (221 | | | | 4 | 7 | Exp 4: DC Power Supply |
| 7 | March 26 April 30 | - Bipolar Junction Transisto transistors current-voltage | Bipolar Junction Transistors (BJTs): structure and operation, types, symbols and convention transistors current-voltage characteristics. | | | 5 | 1.1-1.3, 1.5, 1.6, 2, 3 | Exp 5: MOSFET Amplifiers |
| 8 | | April 2 – 6 BJT circuits at DC, Biasing, Small signal models and analysis. | | | | | 4-6 | Exp 6: BJT Characteristics |
| lid | term Vacatio | n April 9-13 | | | | | | |
| 9 | April 16 – | U U I | Single stage amplifier (CE, and CB). | | | 5 | 7.1-7.5 | No Lab |
| .0 | April 23 – | 27 Single stage amplifier (CC Differential Amplifiers: M | | | | | 7.6 , 7.7 1,2 | Exp 7: BJT CE Amplifiers |
| 1 | April 30 – M | BJT Differential amplifiers Digital Circuit design over | | | | 7 | 3 1.1, 1.2, 2.1, 2.2 | No Lab |
| Exa | m 2 Wednes | day May 4 (6:00-8:00 pm). Exa | m location: Building 22 room 119 | for both sections. | | ' | | |
| 12 | May 7-1 | CMOS Logic circuits, CM | OS transistor sizing. | | | 10 | 3.1-3.8 | Exp 8: Differential Amp. |
| 13 | May 14-1 | Pass transistor logic circuit basic BJT inverter. | Pass transistor logic circuits (PTL), Basic concept of dynamic lebasic BJT inverter. | | ogic circuits. BJT as a switch, The | | 4.1, 4.2, 5,6.1 3.4, 10 | Exp 9: CMOS Inverter |
| 14 | May 21-2 | | RTL circuits, maximum fan-out calculation, ECL logic circuits. | | | | 7.1, 7.3, 7.4, 7.7 | Exp 10: BJT Logic Gates |
| 15 | May 28 - Ju | ay 28 - June 1 TTL Basic Inverters and NAND gate, BJT vs. MOS Logic: advantage/disadvantages. | | | | 11 | Handout | Lab Final |
| · | 1 E C | lay June 12 2011 @ 7:00PM | | _ | | | | |

Final Exam Sunday June 12, 2011 @ 7:00PM